

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Linthicum, Kevin J.

Serial Number: Unassigned

Filed: Concurrently Herewith

Related Application Info:

Ser. No. 09/850,687

Filed: May 7, 2001

For: PENDEOEPIITAXIAL METHODS OF FABRICATING GALLIUM NITRIDE SEMICONDUCTOR LAYERS ON SILICON WAFERS OR WAFERS CONTAINING SILICON, AND GALLIUM NITRIDE SEMICONDUCTOR STRUCTURES FABRICATED THEREBY

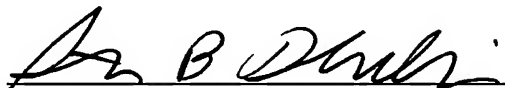
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It is respectfully requested that the document(s) listed on the attached Form PTO/1449 be considered by the Patent and Trademark Office in the above-referenced application and made of record therein. All items listed on the PTO/1449 were cited in parent application Serial No. 09/850,687, filed November 24, 1998. Since the benefit of this application is claimed under 35 U.S.C. §120, no copies need to be furnished in accordance with 37 C.F.R. §1.98(d); however, copies will be furnished on request.

Respectfully submitted,

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August 4, 2003

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Patricia L. Pontello

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Attorney Docket No. 5051-448CT

Serial No.: To Be Assigned

LIST OF DOCUMENTS CITED BY APPLICANT
(Use several sheets if necessary)Applicants:
Kevin J. Linthicum, et al.Filing Date:
Concurrently Herewith

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